WHAT IS CLAIMED IS:

1. A semiconductor device, comprising:

a semiconductor element;

a plurality of lead wires connected to a plurality of connecting electrodes of said semiconductor element;

at least a single dummy lead wire that does not include an outer lead portion for electrically connecting said semiconductor element to an external circuit of said semiconductor element;

an insulating film having an opening portion for accommodating said semiconductor element and serving to support said lead wires connected to the connecting electrodes of the semiconductor element and said dummy lead wire; and

a resin molding covering the connecting portion between the tip portions of the lead wires and the connecting electrodes and the tip portion of said dummy lead wire within the opening portion of said insulating film.

2. The semiconductor device according to claim 1, wherein the tip portion of the dummy lead wire covered with said resin molding is positioned between the peripheral portion of said opening portion and the peripheral portion of the semiconductor element arranged within the opening portion.

3. The semiconductor device according to claim 1, wherein the tip portion of said dummy lead wire extends

over said semiconductor element.

4. The semiconductor device according to claim 1, wherein said dummy lead wire is arranged in a large space having at least twice the minimum pitch of the arrangement of said lead wires.

5. The semiconductor device according to claim 1, wherein at least two dummy lead wires are arranged in said semiconductor device and the tip portions of two adjacent dummy lead wires are connected to each other.

6. The semiconductor device according to claim 1, wherein said dummy lead wires are formed in two sides, which face each other, of said semiconductor element, and the tip portions of the dummy lead wires positioned to face each other are connected to each other.

7. The semiconductor device according to claim 1, wherein said semiconductor element includes a dummy connection electrode that is not electrically connected to an internal circuit, and the tip of said dummy lead wire is connected to said dummy connection electrode.

8. The semiconductor device according to claim 2, wherein said dummy lead wire is arranged in a large space having at least twice the minimum pitch of the arrangement of said lead wires.

9. The semiconductor device according to claim 2, wherein at least two dummy lead wires are arranged in said semiconductor device and the tip portions of two

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adjacent dummy lead wires are connected to each other.

10. The semiconductor device according to claim 3, wherein said dummy lead wire is arranged in a large space having at least twice the minimum pitch of the arrangement of said lead wires.

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11. The semiconductor device according to claim 3, wherein at least two dummy lead wires are arranged in said semiconductor device and the tip portions of two adjacent dummy lead wires are connected to each other.

12. The semiconductor device according to claim 3, wherein said dummy lead wires are formed in two sides, which face each other, of said semiconductor element, and the tip portions of the dummy lead wires positioned to face each other are connected to each other.

13. The semiconductor device according to claim 3, wherein said semiconductor element includes a dummy connection electrode that is not electrically connected to an internal circuit, and the tip of said dummy lead wire is connected to said dummy connection electrode.

14. The semiconductor device according to claim 4, wherein at least two dummy lead wires are arranged in said semiconductor device and the tip portions of two adjacent dummy lead wires are connected to each other.

15. The semiconductor device according to claim 4, wherein said dummy lead wires are formed in two sides, which face each other, of said semiconductor element, and the tip portions of the dummy lead wires positioned

to face each other are connected to each other.

16. The semiconductor device according to claim 4, wherein said semiconductor element includes a dummy connection electrode that is not electrically connected to an internal circuit, and the tip of said dummy lead wire is connected to said dummy connection electrode.

17. The semiconductor device according to claim 7, wherein said dummy connection electrode is electrically connected to a power source line or a ground line.

18. The semiconductor device according to claim 8, wherein at least two dummy lead wires are arranged in said semiconductor device and the tip portions of two adjacent dummy lead wires are connected to each other.

19. The semiconductor device according to claim 8, wherein said dummy lead wires are formed in two sides, which face each other, of said semiconductor element, and the tip portions of the dummy lead wires positioned to face each other are connected to each other.

20. The semiconductor device according to claim 8, wherein said semiconductor element includes a dummy connection electrode that is not electrically connected to an internal circuit, and the tip of said dummy lead wire is connected to said dummy connection electrode.

21. The semiconductor device according to claim 10, wherein at least two dummy lead wires are arranged in said semiconductor device and the tip portions of two adjacent dummy lead wires are connected

to each other.

22. The semiconductor device according to claim 10, wherein said dummy lead wires are formed in two sides, which face each other, of said semiconductor element, and the tip portions of the dummy lead wires positioned to face each other are connected to each other.

23. The semiconductor device according to claim 10, wherein said semiconductor element includes a dummy connection electrode that is not electrically connected to an internal circuit, and the tip of said dummy lead wire is connected to said dummy connection electrode.

24. The semiconductor device according to claim 13, wherein said dummy connection electrode is electrically connected to a power source line or a ground line.

25. The semiconductor device according to claim 16, wherein said dummy connection electrode is electrically connected to a power source line or a ground line.

26. The semiconductor device according to claim 20, wherein said dummy connection electrode is electrically connected to a power source line or a ground line.

27. The semiconductor device according to claim 23, wherein said dummy connection electrode

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is electrically connected to a power source line or a ground line.